

## APPLICATION DATA SHEET

### Application Information

Application Type:: Regular  
Subject Matter:: Utility  
Title:: SILICON ON INSULATOR STRUCTURE  
FROM LOW DEFECT DENSITY SINGLE  
CRYSTAL SILICON  
Attorney Docket Number:: MEMC 98-3052 (2512.2)  
Request for Early Publication?:: No  
Request for Non-Publication?:: No  
Total Drawing Sheets:: 35  
Small Entity?:: No  
Petition Included?:: No  
Secrecy Order in Parent?:: No

### Applicant Information

Applicant Authority Type:: Inventor  
Primary Citizenship Country:: US  
Status:: Full Capacity  
Given Name:: Robert  
Middle Name:: J.  
Family Name:: Falster  
City of Residence:: London  
Country of Residence:: England  
Street of Mailing Address:: 508 Pearl Drive, P.O. Box 8  
City of Mailing Address:: St. Peters  
State or Province of Mailing  
Address:: MO  
Postal Code of Mailing Address:: 63376

### Correspondence Information

Correspondence Customer Number:: 000321

**Representative Information**

Representative Customer Number:: 000321

**Domestic Priority Information**

| Application::    | Continuity<br>Type::   | Parent<br>Application:: | Parent Filing<br>Date:: |
|------------------|------------------------|-------------------------|-------------------------|
| This application | Division of            | 09/737,715              | 12/15/00                |
| 09/737,715       | Continuation<br>of     | 09/387,288              | 08/31/99                |
| 09/387,288       | Non-<br>Provisional of | 60/098,902              | 09/02/98                |

**Assignee Information**

Assignee Name::

MEMC Electronic Materials, Inc.